

isc Silicon PNP Power Transistor
2SB632
DESCRIPTION

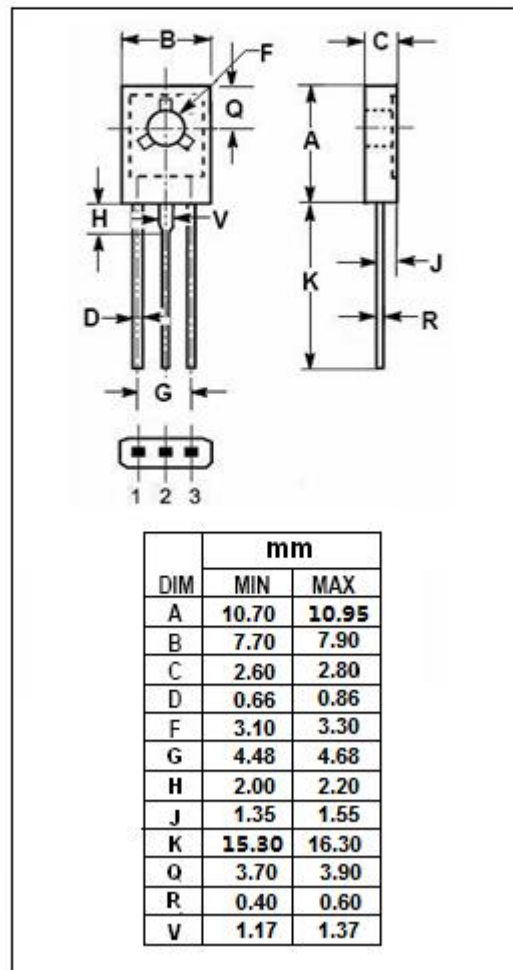
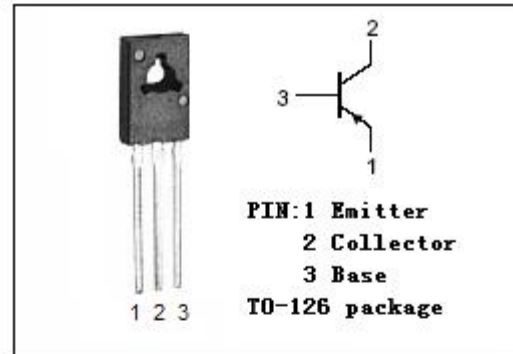
- High Collector Current- $I_C=-2.0A$
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO}=-25V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SD612
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Low-frequency power amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CP}	Collector Current-Pulse	-3	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	10	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -10 μA ; I _E = 0	-25			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA ; R _{BE} = ∞	-25			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -10 μA ; I _C =0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1.5A ; I _B = -0.15A			-0.9	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -1.5A ; I _B = -0.15A			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -20V ; I _E = 0			-1	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V ; I _C = 0			-1	μA
h _{FE-1}	DC Current Gain	I _C = -500mA ; V _{CE} = -2V	60		320	
h _{FE-2}	DC Current Gain	I _C = -1.5A ; V _{CE} = -2V	30			
f _T	Current-Gain—Bandwidth Product	I _C = -50mA ; V _{CE} = -10V		100		MHz
C _{OB}	Output Capacitance	I _E =0 ; V _{CB} = -10V, f _{test} = 1MHz		45		pF

Switching times

t _{on}	Turn-On Time	I _C = -500mA , R _L = 24 Ω , I _{B1} = -I _{B2} = -50mA, V _{CE} = -12V		0.06		μs
t _{off}	Turn-Off Time			0.08		μs
t _{stg}	Storage Time			0.4		μs

◆ h_{FE-1} Classifications

D	E	F
60-120	100-200	160-320

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